

# 3/12/14 phonon physics - Lindhard Theory

Bands  $\gamma$ 's &  $n$ 's

Atomic Hydrogen



Electrons



Nuclei

Germanium

0.69 eV Gap  
valence

Semiconductor  $\rightarrow$  Gap  $< 3$  eV

$\rightarrow$  Because of thermal fluctuations Germanium conducts at room temperatures

For nuclear recoils, when the nucleus begins to move it can either interact with electrons & excite them or interact with other nuclei and give up some energy to heat (phonons) so there is a quenching factor

$$Q = \frac{E_{nr}}{E_{er}} \rightarrow \text{energy recoil less energy given to phonons} \Rightarrow \text{energy recoil}$$

So Lindhard derivation tries to separate energy loss to electrons and energy loss to nuclei.

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# 4/16/14 - phonon physics - 1D dimensional lattice

discrete

$$F_s = \sum_n C_n (q_{sn} - q_s) = m \frac{d^2 q_s}{dt^2}$$

then derive wave eqn.

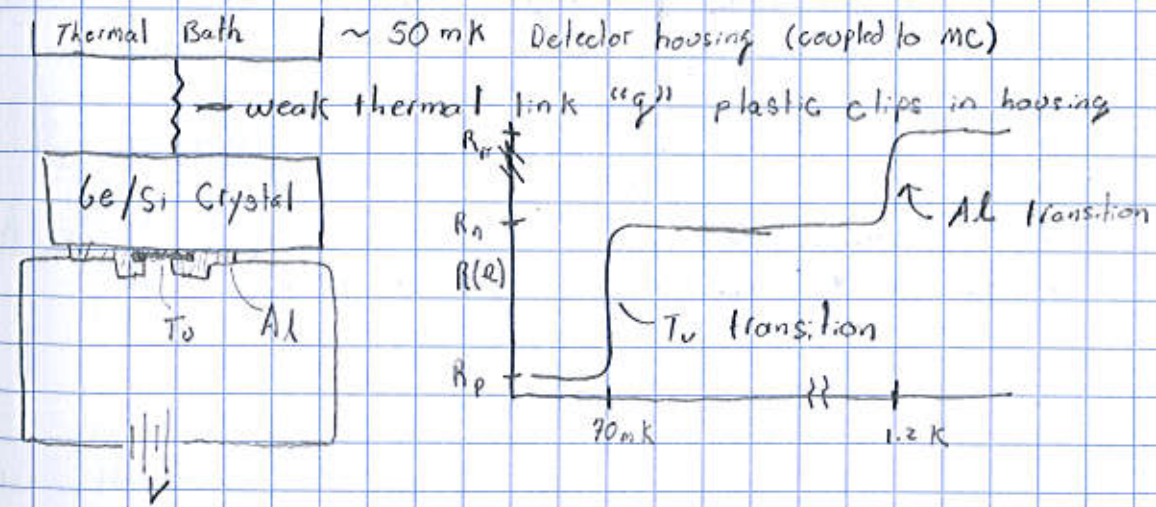
$$\frac{d^2 q}{dt^2} = v^2 \frac{d^2 q}{dx^2} \Rightarrow q \sim A e^{-i\omega(t - \frac{x}{v})}$$

$$\omega / \text{definition} \quad \frac{\omega \lambda}{v} = 2\pi \Rightarrow \frac{\omega}{v} = \frac{2\pi}{\lambda} = k$$

$$q = A e^{-i\omega t + i k x} \rightarrow \text{use to get dispersion relation for } \lambda \approx a$$

$$\omega_n^2 = \frac{2}{m} \sum_{n>0} C_n (1 - \cos(nka))$$

# 4/23/14 Electrothermal Feedback / TES (my talk which I postponed)

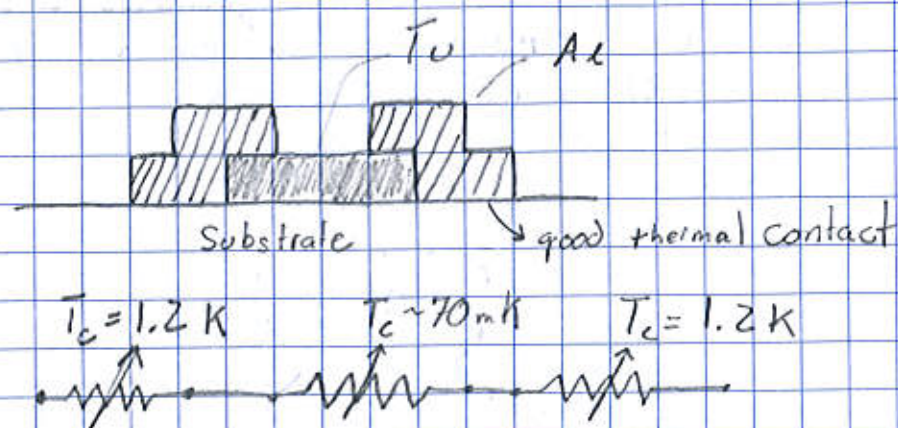


We want to operate at the  $T_c$  transition and use the deeply superconducting Al Sins as Quasi particle traps - see Allison's talk.

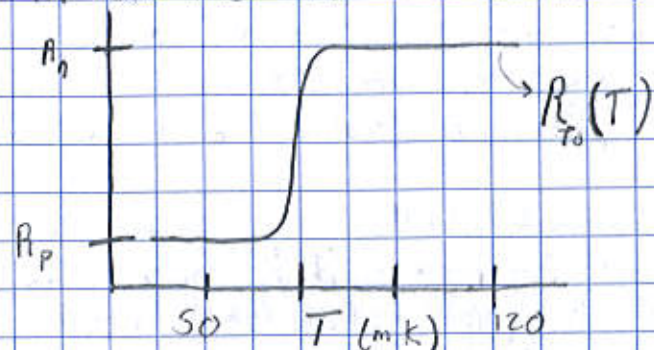
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So the Aluminum/Tungsten structure is called a Transition Edge Sensor (TES). This can be modeled as below

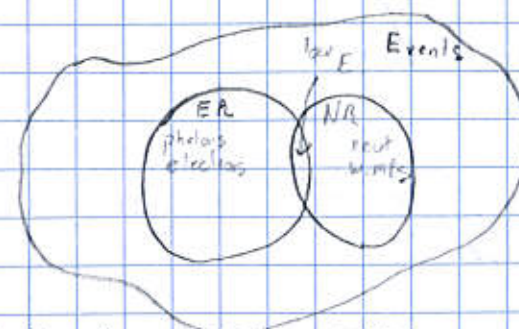


Zooming in on the  $T_u$  transition



### ETF/AET presentation

- 1) Because of nature of DM we want a pure NR sample at low E
- 1) Hassan has said Charge will be quenched with phonons. So NRs  $\Rightarrow$  measure both you might be able to do ER/NR discrim

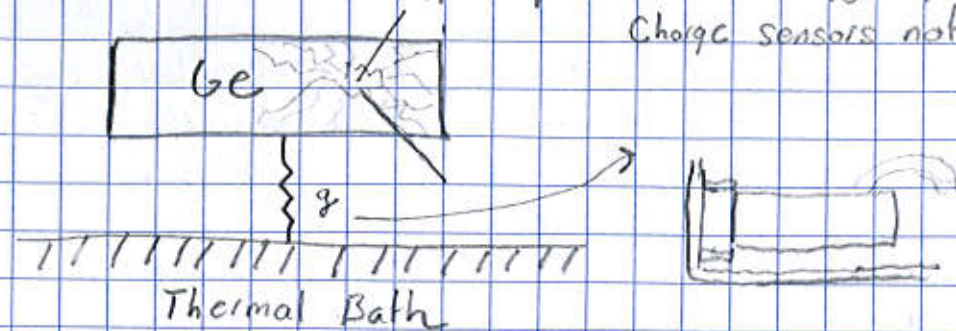


- 2) Allison talked about TES and absorbing phonons by Quasiparticle trapping - getting quasiparticles (Broken Cooper pairs) to disperse to an active element and stay there making an affect on a measurable bulk property of the element (resistance)
- 3) Today: how to set it up so that these sensors will be stably operating to measure 'heat' from a particle event and return to normal.

Review: TES (previous two pages, draw simple substrate not whole detector)

So, need to put these things on a substrate and use them to measure phonons.





To operate a TES on this substrate we must balance power

$$\delta P = (\text{Power dumped electrically}) - (\text{Cooling power through link}) + (\text{Signal Power})$$

Suppose we tried current bias:  $I_b$   
 have control here

$$C_v \frac{dT}{dt} = I_b^2 R(T) - K(T^n - T_s^n) + P(t)$$

(positive FB)       $\underbrace{\quad}_{\text{Signal}}$

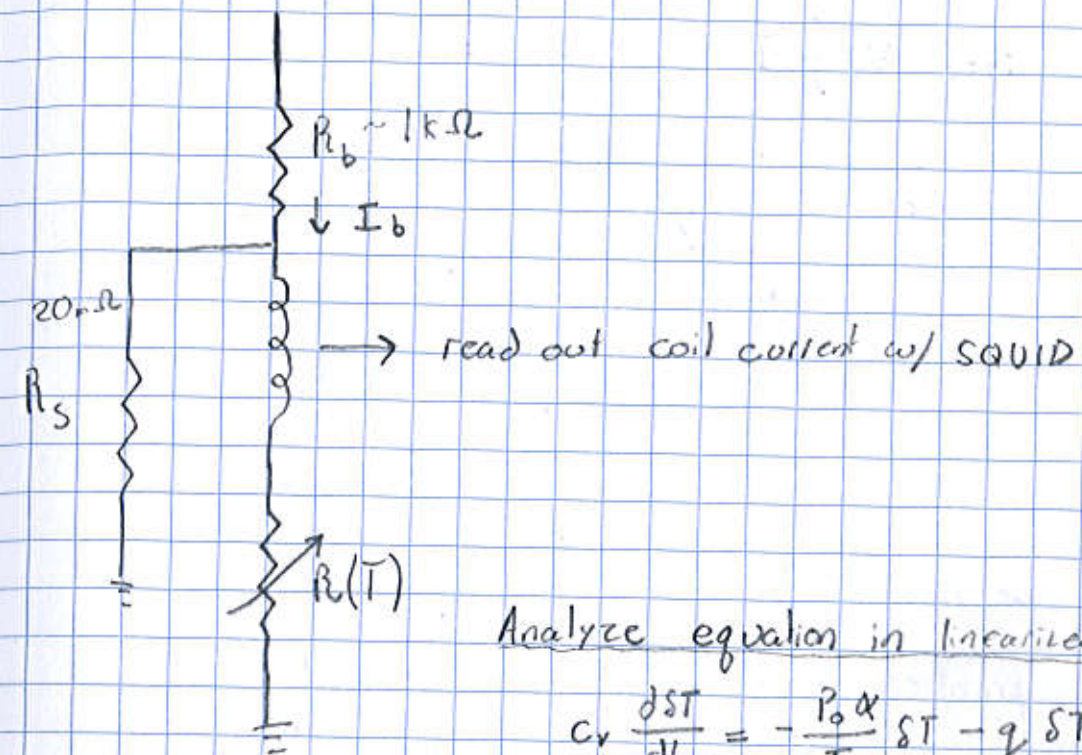
$$P_e = IV = I^2 R$$

$$C_v \frac{dT}{dt} = \frac{V_b^2}{R(T)} - K(T^n - T_s^n) + P(t)$$

(negative FB)       $\underbrace{\quad}_{\text{Signal}}$

$$P_e = IV = \frac{V^2}{R}$$

So, want to use negative ETF



Analyze equation in linearized Approx.

$$C_v \frac{\delta T}{dt} = -\frac{P_0 \alpha}{T} \delta T - q \delta T$$

$P_0$  = equilibrium power flowing to substrate

$$\alpha = \frac{T}{R} \frac{\partial R}{\partial T}$$

The effective time constant of the eqn is:

$$q = nKT^{n-1}$$

$$\tau_{ETF} = \frac{\tau_0}{1 + \frac{q}{n}}$$

$$n=5$$

$\tau_0 = (C_v/K)$  natural conductive time const

here we've modeled a pulse as an instantaneous temperature excursion. This is like assuming the events raise the temperature discretely and ETF brings them back. Or the time constants for Quasiparticle transport are slower than  $\tau_{ETF}$



The energy of the signal is

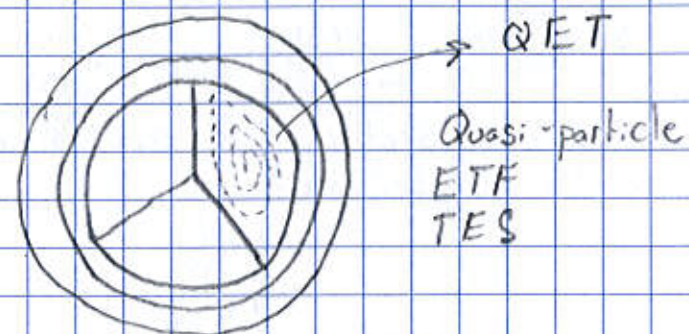
$$E_{TES} = V_b \int SI dt$$

and so (See Sunil's thesis App B) for an exponential phonon pulse governed by  $\tau_{ETF}$  the noise is: including Johnson noise on the sensor and phonon thermal noise

$$\sigma = \sqrt{4 k_B T^2 C_v \underbrace{(\sqrt{n/2}/\alpha)}_{\text{ETF assistance}}} \quad (\text{Sec. K Irwin})$$

well, where is  $T_c$ ? inside  $\alpha$ !

So, in practice many TES are connected in parallel and load out on the substrate



A specific model for  $R(T)$  can be used to get more accurate estimates for our noise and specifically the dependence on  $T_c$

possible next topics

- 1) Full derivation of  $\sigma$  using optimal filter framework
- 2) Specific calculation for reasonable models of  $R(T)$  including Johnson noise of all resistors
- 3) Fixing the above for the ETF cutoff